Figure 3-4 Side view of the photomasks pattern.

Figure 3-5 Top view of the combined photomasks pattern.
Layer 1 (40µm)  

Layer 2 (40µm)  

Layer 3 (40µm)  

Layer 1 (80µm)  

Layer 2 (80µm)  

Layer 3 (80µm)  

Figure 3-6 Plan view of the photomasks pattern where shadowed region represents the Cr doped region.
Figure 4-1 SEM micrograph of 1.8 x 80 μm pseudomorphic MODFET with 5 μm drain-source spacing
Figure 4-8 SEM micrographic investigation on gate length of the pMODFET.